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(71) Applicant (*for all designated States except US*): **TECH-
NIC, INC.** [US/US]; 111 East Ames Court, Plainview, NY
11803 (US).

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(72) Inventors; and
(75) Inventors/Applicants (*for US only*): **SCHETTY, Robert,
A., III** [US/US]; 23 Paddock Drive, Ft. Salogna, NY
11768 (US). **VICKERS, Winnie, Ruth** [US/US]; 42
Driving Park, Lynbrook, NY 11563 (US).

(74) Agents: **FANUCCI, Allan, A.** et al.; Winston & Strawn,
Patent Department, 1400 L Street, N.W., Washington, DC
20005 (US).

(54) Title: MINIMIZING WHISKER GROWTH IN TIN ELECTRODEPOSITS

(57) Abstract: The present invention relates to a method for reducing tin whisker formation in tin deposits by plating on an under-lying metal tin deposits which are essentially free of compressive stress or are predominantly in a predetermined crystal orientation that essentially matches that of the underlying metal in order to inhibit tin whisker growth. The deposits preferably exhibit no com-pressive stress or exhibit a tensile stress. Also, the most preferred crystal orientation is one that is the same as that of the underlying metal. The deposit preferably contains at least 95 % tin and optionally at least one alloying element of silver, bismuth, copper or zinc in an amount of 5 % or less. Advantageously, the tin deposits are provided during electroplating from a specially formulated plating solution that contains a crystal orientation surfactant.



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